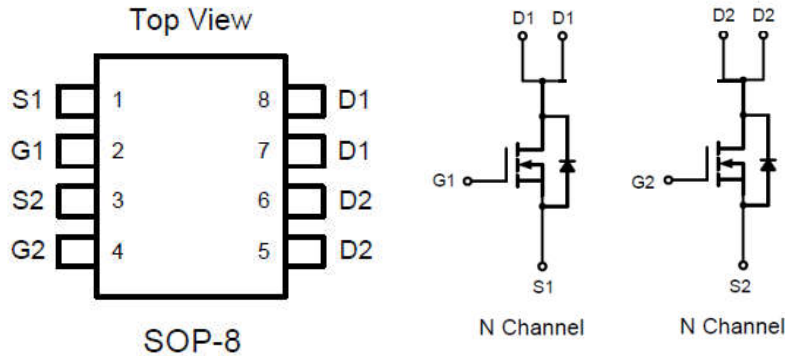


## General Description

The CX3203 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

## Pin Description



## Featuration

- N-Channel  
36V/7A,  
 $R_{DS(ON)}=20m\Omega$  (MAX.) @  $V_{GS}=10V$   
 $R_{DS(ON)}=30m\Omega$  (MAX.) @  $V_{GS}=4.5V$
- Super High Dense Cell Design
  - Reliable and Rugged

## Applications

- Power Management in Notebook Computer
- Portable Equipment
- Battery Powered Systems

### Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

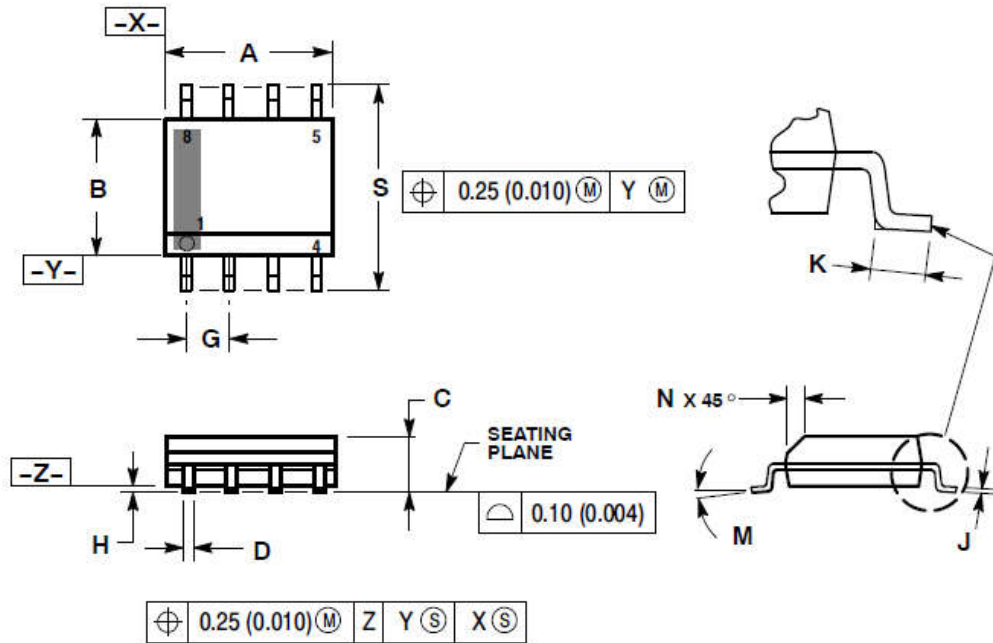
Parameter	Symbol	Value		Units
		N1	N2	
Drain to Source Voltage	$V_{DSS}$	36	36	V
Gate to Source Voltage	$V_{GSS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current	$I_D$	25 $^\circ\text{C}$	7	A
		85 $^\circ\text{C}$	5.6	A
Pulsed Drain Current	$I_{D(pulse)}$	28	28	A
Maximum Power Dissipation	$P_D(25^\circ\text{C})$	1.5		W
Operating Junction Temperature	$T_J$	+150		$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55-+150		$^\circ\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	$T_L$	260		$^\circ\text{C}$

### Electrical Characteristics ( $T_A = 25^\circ\text{C}$ )

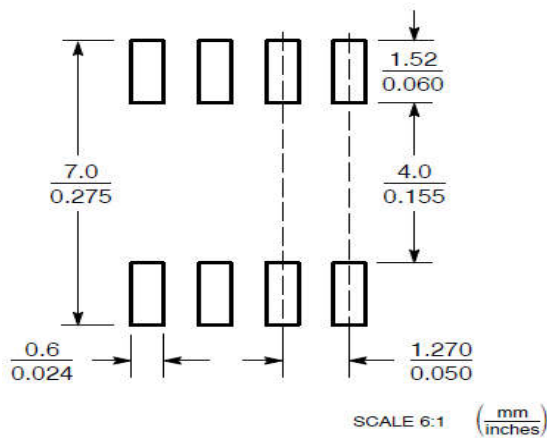
Parameter	Symbol	Test Conditions	MIN	TYP	MAX	Units
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_{DS}=250\mu A$	36			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30V, V_{GS}=0V$			1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
Gate threshold voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	2.0	2.5	V
Drain to Source On-state Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=3.0A$		15	20	$m\Omega$
		$V_{GS}=4.5V, I_D=3.0A$		25	30	$m\Omega$
Input Capacitance	$C_{ISS}$	$V_{DS}=20V, V_{GS}=0V, f=1MHz$		570		pF
Output Capacitance	$C_{OSS}$			80		pF
Reverse Transfer Capacitance	$C_{RSS}$			67		pF
Total Gate Charge	$Q_g$	$V_{DS}=24V, V_{GS}=10V, I_D=7A$		6.2		nC
Gate-Source Charge	$Q_{gs}$			2.4		nC
Gate-Drain Charge	$Q_{gd}$			2.3		nC
Drain-Source Diode Forward Voltage	$V_{SD}$	$I_S=1.0A, V_{GS}=0V$		0.8	1.3	V

### Package Dimensions:

### SOP-8



#### SOLDERING FOOTPRINT\*



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244